Akira Ishibashi

List of Publications by Year
in descending order

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83	1,050	471509 17	454955 30
papers	citations	h-index	g-index

83	83	83	545
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Quaternary alloyZn1â^'xMgxSySe1â^'y. Physical Review B, 1998, 57, 2257-2263.	3.2	136
2	Gated time projection chamber. Nuclear Instruments & Methods in Physics Research, 1983, 212, 273-280.	0.9	79
3	Epitaxial growth ofpâ€type ZnMgSSe. Applied Physics Letters, 1994, 64, 904-906.	3.3	77
4	A proposal of a vacuum micro quantum interference transistor. Journal of Applied Physics, 1993, 73, 1-7.	2.5	54
5	ZnCdSe/ZnSSe/ZnMgSSe SCH Laser Diode with a GaAs Buffer Layer. Japanese Journal of Applied Physics, 1994, 33, L938-L940.	1.5	53
6	Advances in blue laser diodes. Journal of Crystal Growth, 1994, 138, 677-685.	1.5	49
7	Current status and future prospects of ZnSe-based light-emitting devices. Journal of Crystal Growth, 2000, 214-215, 1029-1034.	1.5	49
8	Operation and dynamics of ZnSe/ZnMgSSe double heterostructure blue laser diode at room temperature. Applied Physics Letters, 1995, 66, 656-658.	3.3	37
9	Quasiâ€twoâ€dimensional exciton in ZnSe/ZnMgSSe single quantum well. Applied Physics Letters, 1995, 66, 180-182.	3.3	34
10	Epitaxial growth of ZnMgTe and double heterostructure of on GaAs substrate by metalorganic chemical vapor deposition. Journal of Crystal Growth, 1995, 156, 373-376.	1.5	33
11	491-nm ZnCeSe/ZnSe/ZnMgSSe SCH Laser Diode with a Low Operating Voltage. Japanese Journal of Applied Physics, 1993, 32, L1530-L1532.	1.5	25
12	Microscopic defect induced slow-mode degradation in IIâ€"VI based blueâ€"green laser diodes. Journal of Crystal Growth, 2000, 214-215, 1035-1039.	1.5	24
13	Heterointerface Field Effect Transistor with 200 A-Long Gate. Japanese Journal of Applied Physics, 1988, 27, L2382-L2384.	1.5	23
14	ZnCdSe/ZnSe/ZnMgSSe Separate-Confinement Heterostructure Laser Diode with Various Cd Mole Fractions. Japanese Journal of Applied Physics, 1994, 33, L639-L642.	1.5	23
15	Optimized ZnSe:N/ZnTe:N contact structure of ZnSe-based IIâ€"VI laser diodes. Applied Physics Letters, 1998, 73, 235-237.	3.3	22
16	Optical measurement of the ambipolar diffusion length in a ZnCdSeâ€"ZnSe single quantum well. Journal of Applied Physics, 1997, 81, 536-538.	2.5	21
17	Carrier-density dependence of the photoluminescence lifetimes in ZnCdSe/ZnSSe quantum wells at room temperature. Applied Physics Letters, 1999, 74, 3359-3361.	3.3	19
18	Energy Spectrum of Two-Dimensional Electron Gas to be Used in Quantum Cross Structures. Japanese Journal of Applied Physics, 2006, 45, 9137-9139.	1.5	17

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19	Theoretical and experimental results of electronic transport of spin quantum cross structure devices. Journal of Applied Physics, 2009, 105, 07D522.	2.5	17
20	Electron-beam-induced resist and aluminum formation. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1991, 9, 169.	1.6	15
21	Defect annealing in a IIâ€“VI laser diode structure under intense optical excitation. Applied Physics Letters, 1998, 72, 194-196.	3.3	14
22	High-Efficiency ZnCdSe/ZnSSe/ZnMgSSe Green Light-Emitting Diodes. Optical Review, 1995, 2, 167-170.	2.0	13
23	Study of very low airborne particle count in clean-unit system platform. Review of Scientific Instruments, 2005, 76, 085111.	1.3	13
24	Surface Morphology of Gold Thin Films Deposited on Poly(ethylene naphthalate) Organic Films for Quantum Cross Devices. Japanese Journal of Applied Physics, 2008, 47, 244-248.	1.5	13
25	Ultra-High Cleanliness of ISO Class Minus 1 Measured in Triply Connected Clean-Unit System Platform. Japanese Journal of Applied Physics, 2008, 47, 5712.	1.5	13
26	Nanopatterns induced by pulsed laser irradiation on the surface of an Fe-Al alloy and their magnetic properties. Applied Physics Letters, 2013, 102, .	3.3	12
27	High-efficiency ZnCdSe/ZnSSe/ZnMgSSe green and blue light-emitting diodes. , 1996, , .		11
28	Effect of Coulomb enhancement on optical gain in (Zn,Cd)Se/ZnSe multiple quantum wells. Physical Review B, 1996, 54, 16417-16420.	3.2	10
29	Ni thin films vacuum-evaporated on polyethylene naphthalate substrates with and without the application of magnetic field. Applied Surface Science, 2009, 255, 3706-3712.	6.1	10
30	Room-Temperature Operation of ZnSe-Active-Layer and ZnCdSe-Active-Layer Laser Diodes. Japanese Journal of Applied Physics, 1996, 35, 1410-1414.	1.5	9
31	Surface Roughness and Magnetic Properties of Ni and ${m Ni}_{78}{m Fe}_{22}$ Thin Films on Polyethylene Naphthalate Organic Substrates. IEEE Transactions on Magnetics, 2010, 46, 1356-1359.	2.1	9
32	Optical Simulation for Multi-Striped Orthogonal Photon-Photocarrier-Propagation Solar Cell (MOP3SC) with Redirection Waveguide. 3D Research, 2016, 7, 1.	1.8	8
33	High temperature gain measurements in optically pumped ZnCdSe-ZnSe quantum wells. IEE Proceedings: Optoelectronics, 1996, 143, 110-112.	0.8	8
34	Theoretical Investigation of New Quantum-Cross-Structure Device as a Candidate beyond CMOS. Materials Research Society Symposia Proceedings, 2008, 1067, 1.	0.1	7
35	Growth of ZnMgSSe and a blue-laser diode. Microelectronics Journal, 1994, 25, 643-649.	2.0	6
36	Distribution of chalcogen atoms in ZnSSe and ZnMgSSe: an EXAFS study. Journal of Crystal Growth, 1996, 159, 41-44.	1.5	6

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37	Surface morphologies and magnetic properties of Fe and Co magnetic thin films on polyethylene naphthalate organic substrates. Journal of Applied Physics, 2012, 111, 07C104.	2.5	6
38	Study of the growth mechanism of ZnCdSe by MBE using the mass spectrometer. Journal of Crystal Growth, 1998, 193, 43-49.	1.5	5
39	Physical Analysis of Connected Clean Units in Clean-Unit System Platform. Japanese Journal of Applied Physics, 2006, 45, 6481-6483.	1.5	5
40	Metalorganic chemical vapor deposition on mesoscopicâ€structured substrates with closed topologies. Journal of Applied Physics, 1991, 70, 2117-2122.	2.5	4
41	Extended X-Ray Absorption Fine Structure Study of ZnSSe and ZnMgSSe. Japanese Journal of Applied Physics, 1995, 34, L539-L542.	1.5	4
42	Degradation in II-VI Laser Diodes. Materials Science Forum, 1997, 258-263, 1329-1334.	0.3	4
43	Ultrasmooth Ni thin films evaporated on polyethylene naphthalate films for spin quantum cross devices. Journal of Applied Physics, 2008, 103, 07B523.	2.5	4
44	The fabrication of Ni quantum cross devices with a 17 nm junction and their currentâ€“voltage characteristics. Nanotechnology, 2010, 21, 015301.	2.6	4
45	Redirection Waveguide having Discrete Translational Symmetry for Photovoltaic Systems with Solar-Cell Units Placed at the Periphery. Energies, 2018, 11, 3498.	3.1	4
46	Lifting Off Spatial Degeneracy of Functions, Where Does It Lead Us for Photovoltaic Device Systems?. Energies, 2020, 13, 5234.	3.1	4
47	Advanced fabrication techniques of three-dimensional microstructures for future electronic devices. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1994, 12, 3160.	1.6	3
48	ZnSe nitrogen doping using an ion-free electron-cyclotron-resonance plasma beam. Applied Physics Letters, 1997, 70, 1453-1455.	3.3	3
49	Growth mechanism of IIâ€“VI compound semiconductors by molecular beam epitaxy. Journal of Crystal Growth, 1997, 175-176, 587-592.	1.5	3
50	Currentâ€“Voltage Characteristics in Nanoscale Tunnel Junctions Utilizing Thin-Film Edges. Japanese Journal of Applied Physics, 2010, 49, 105203.	1.5	3
51	Focused Magneto-Optic Kerr Effect Spectroscopy in Ni75Fe25and Fe Ferromagnetic Thin Films on Organic Substrates. Japanese Journal of Applied Physics, 2013, 52, 013001.	1.5	3
52	Improvement of Minority Carrier Lifetime by HCN Treatments. ECS Journal of Solid State Science and Technology, 2013, 2, Q127-Q130.	1.8	3
53	<title>Blue/green laser diodes based on ZnMgSSe</title>. , 1994, , .		2
54	Optical gain in ZnCdSe-ZnSe quantum well structures. , 1996, , .		2

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55	Surface Roughening and Composition Modulation of ZnSe-related II-VI epitaxial films. Materials Research Society Symposia Proceedings, 1996, 448, 159.	0.1	2
56	Channelled-substrate planar waveguided green laser diodes. Journal of Crystal Growth, 1996, 159, 1172.	1.5	2
57	Study of Gold Thin Films Evaporated on Polyethylene Naphthalate Films toward the Fabrication of Quantum Cross Devices. Materials Research Society Symposia Proceedings, 2007, 1025, 1.	0.1	2
58	Recovery of degradation in II-VI laser diode structure. Electronics Letters, 1999, 35, 1281.	1.0	2
59	The Tent-type Clean Unit System Platform for Air Cleaning and Non-contact Sleep Assessment. , 2019, , .		2
60	Reply to â€œComment on â€˜Quaternary alloyZn1â^'xMgxSySe1â^'yâ€™ â€• Physical Review B, 1998, 58, 11054-11054.	1.0	1
61	Current status and perspective of ZnMgSSe-based II-VI laser diodes. , 1999, , .		1
62	Quantum-Cross Tunneling Junction for High Density Memory. Materials Research Society Symposia Proceedings, 2006, 961, 1.	0.1	1
63	Fabrication of Nickel/Organic-Molecule/Nickel Nanoscale Junctions Utilizing Thin-Film Edges and Their Structural and Electrical Properties. Japanese Journal of Applied Physics, 2012, 51, 065202.	1.5	1
64	Fabrication of Nickel/Organic-Molecule/Nickel Nanoscale Junctions Utilizing Thin-Film Edges and Their Structural and Electrical Properties. Japanese Journal of Applied Physics, 2012, 51, 065202.	1.5	1
65	<title>Room-temperature continuous wave emission of II-VI laser diodes</title>. , 1994, , .		0
66	Structural Study of Degraded II-VI Blue-Light Emitters. Materials Science Forum, 1995, 196-201, 1109-1116.	0.3	0
67	Room temperature photo-pumped lasing action of ZnCdSe/ZnSe/ZnMgSSe double heterostructure grown by metal-organic chemical vapor deposition. , 1996, , .		0
68	<title>Optical pickup using a blue-green laser diode to read a high-density disk</title>. , 1997, 3109, 128.		0
69	<title>ZnMgSSe-based laser diodes</title>. , 1997, 2994, 22.		0
70	Device characteristics and degradation of ZnMgSSe-based semiconductor lasers. Electronics and Communications in Japan, 1998, 81, 27-34.	0.2	0
71	Deep defect center characteristics of wide-bandgap II-VI and III-V blue laser materials. , 1998, , .		0
72	Degradation physics of II-VI blue-green laser diodes and LEDs. , 1998, , .		0

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73	Recombination lifetimes in undoped and doped ZnCdSe laser structures. , 1999, 3625, 41.		0
74	A Theoretical Study and Realization of New Spin Quantum Cross Structure Devices using Organic Materials. Materials Research Society Symposia Proceedings, 2009, 1198, 1.	0.1	0
75	Fabrication and Current-Voltage Characteristics of Ni Spin Quantum Cross Devices with P3HT:PCBM Organic Materials. Materials Research Society Symposia Proceedings, 2010, 1252, 8.	0.1	0
76	Large Thermoelectric Voltage in Point Contacts of Ni Ferromagnetic Metals. Materials Research Society Symposia Proceedings, 2011, 1314, 1.	0.1	0
77	Surface Roughness and Magnetic Properties of Co Ferromagnetic Thin Films on Polyethylene Naphthalate Organic Substrates. Journal of the Vacuum Society of Japan, 2012, 55, 187-190.	0.3	0
78	Title is missing!. Journal of the Vacuum Society of Japan, 2008, 51, 211-213.	0.3	0
79	Surface and Interface Structures and Magnetic Properties of Ni and Ni75Fe25 Thin Films on Polyethylene Naphthalate Organic Substrates. Journal of the Vacuum Society of Japan, 2011, 54, 203-206.	0.3	0
80	MOCVD-Grown Atomic Layer Superlattices. NATO ASI Series Series B: Physics, 1989, , 21-44.	0.2	0
81	II. ZnMgSSe-Based Blue Sericonductor Lasers. IEEJ Transactions on Electronics, Information and Systems, 1994, 114, 1222-1227.	0.2	0
82	ZnMgSSe and Related Hetero-structures Grown by Metalorganic Chemical Vapor Deposition. Electrochemistry, 1995, 63, 531-535.	0.3	0
83	Blue Semiconductor Lasers. ZnSe-Based Room-Temperature CW Lasers.. The Review of Laser Engineering, 1997, 25, 504-509.	0.0	0